

Application No.: 10/620,865

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Docket No.: 245402006600

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the claims

Claim 1 (original): A nitride semiconductor laser device chip having a nitride semiconductor stacked-layered structure including an n-type layer, an active layer and a p-type layer successively stacked on a main surface of a nitride semiconductor substrate and having a ridge stripe structure formed in a portion of said p-type layer, wherein

said chip has a length L1 of more than 500  $\mu\text{m}$  in a longitudinal direction of said stripe structure and a length L2 of more than 200  $\mu\text{m}$  in a width direction of said stripe structure, and L1/L2 is more than 2.5.

Claim 2 (original): The nitride semiconductor laser device chip according to claim 1, wherein a total thickness of said nitride semiconductor substrate and said nitride semiconductor stacked-layered structure is more than 50  $\mu\text{m}$  and less than 200  $\mu\text{m}$ .

Claim 3 (original): The nitride semiconductor laser device chip according to claim 1, wherein said stripe structure is formed at a position more than 10  $\mu\text{m}$  away in the width direction of said stripe structure from an edge of said chip.

Claim 4 (original): A nitride semiconductor laser apparatus including the nitride semiconductor laser device chip of claim 1 and a support member for placing the nitride semiconductor laser device chip thereon.

Claim 5 (original): The nitride semiconductor laser apparatus according to claim 4, wherein

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said support member has a larger thermal expansion coefficient as compared to said nitride semiconductor substrate.

Claim 6 (original): The nitride semiconductor laser apparatus according to claim 4, wherein said support member includes one of Al, Ag, Cu, Au, Fe, Al-SiC, CuW and BeO.

Claim 7 (original): The nitride semiconductor laser apparatus according to claim 4, further including a solder for joining said laser device chip to said support member, and said solder including one of AuSn, AgSn, AuSi, AuGe, PbSn, InSn and AgCuSn.

Claim 8 (new): The nitride semiconductor laser apparatus of claim 4, wherein the chip and the nitride semiconductor substrate have a structure of a hexagonal crystal system.

Claim 9 (new): The nitride semiconductor laser apparatus of claim 7, wherein:  
a multilayer metal film comprising an outermost layer comprising Au is formed on a second surface of the nitride semiconductor substrate opposite the main surface; and  
the outermost layer is connected to the support member by the solder.

Claim 10 (new): The nitride semiconductor laser apparatus of claim 7, wherein:  
a multilayer metal film comprising an outermost layer comprising Au is formed on a top surface of the nitride semiconductor stacked-layer structure; and  
the outermost layer is connected to the support member by the solder.

Claim 11 (new): A nitride semiconductor laser apparatus comprising a nitride semiconductor laser device chip and a support member for placing said chip thereon, wherein:

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said chip has a nitride semiconductor stacked-layer structure of a hexagonal crystal system including an n-type layer, an active layer and a p-type layer successively stacked on a first main surface of a nitride semiconductor substrate of the same hexagonal crystal system and has a ridge stripe structure formed in a portion of said p-type layer;

said chip has a length L1 of more than 500  $\mu\text{m}$  in a longitudinal direction of said stripe structure and a length L2 of more than 200  $\mu\text{m}$  in a width direction of said stripe structure, and L1/L2 is more than 2.5; and

a total thickness of said nitride semiconductor substrate and said nitride semiconductor stacked-layer structure is more than 50  $\mu\text{m}$  and less than 200  $\mu\text{m}$ .

Claim 12 (new): The nitride semiconductor laser apparatus of claim 11, wherein said stripe structure is formed at a position more than 10  $\mu\text{m}$  away in the width direction of said stripe structure from an edge of said chip.

Claim 13 (new): The nitride semiconductor laser apparatus of claim 11, wherein said support member has a larger thermal expansion coefficient as compared to said nitride semiconductor substrate.

Claim 14 (new): The nitride semiconductor laser apparatus of claim 11, wherein said support member includes one of Al, Ag, Cu, Au, Fe, Al-SiC, CuW and BeO.

Claim 15 (new): The nitride semiconductor laser apparatus of claim 11, further including a solder for joining said laser device chip to said support member, and said solder including one of AuSn, AgSn, AuGe, PbSn, InSn and AgCuSn.

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Claim 16 (new): The nitride semiconductor laser apparatus of claim 15, wherein:  
a multilayer metal film including an outermost layer of Au is formed on a second main surface of the nitride semiconductor substrate opposite said first main surface; and  
said outermost layer of Au is connected to said support member of by said solder.

Claim 17 (new): The nitride semiconductor laser apparatus of claim 15, wherein:  
a multilayer metal film including an outermost layer of Au is formed on said nitride semiconductor stacked-layer structure; and  
said outermost layer of Au is connected to said support member by said solder.

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